eExam Question Bank

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Question Type	Question	A	B	C	D	Answer	Remark
FBQ	Attenuation is measured in units of _____	decibels	decibel				eExam
FBQ	Attenuators used with coaxial lines are the _____ form while attenuators for use with twisted pair are required to be the _____ form.	unbalanced, balanced	unbalanced, balanced				eExam
FBQ	Frequency bandwidth is expressed in units of _____	hertz	hertz				eExam
FBQ	A filter in which the signal passes through an inductor, or in which a capacitor provides a path to ground, presents less attenuation to low-frequency signals than high-frequency signals and is a _____ filter	low-pass	low-pass				eExam
FBQ	Linear filters whose implementation is based on the combination of resistors (R), inductors (L) and capacitors (C) are collectively known as _____ filters	passive	passive				eExam

☐								
☐	FBQ	For a series RLC circuit, if $f = \frac{1}{2\pi\sqrt{LC}}$, f is the [ ] frequency	resonant	resonance				eExam
☐	FBQ	In a series RLC circuit, the capacitive reactance causes total current to [ ] the applies voltage.	lead	lead				eExam
☐	FBQ	The electrical properties of semiconductors can be modified by addition of impurities to the pure semiconductor substrate. This process is known as [ ]	doping	doping				eExam
☐	FBQ	For reactive loads, maximum power transfer takes place when the source impedance is the complex [ ] of the load impedance	conjugate	conjugate				eExam
☐	FBQ	Electrical impedance has both magnitude and [ ] angle	phase	phase				eExam
☐	FBQ	The impedance of a lossless idealized network element is referred to as [ ]	reactance	reactance				eExam
☐	FBQ	The conduction mechanism in semiconductors is contributed to by both electrons and [ ]	holes	holes				eExam

☐								
☐	FBQ	Circuit elements which have a linear voltage to current relationship and which obey Ohm's Law are referred to as _____ devices	ohmic	ohmic				eExam
☐	FBQ	An electronic device that reduces the amplitude or power of a signal without appreciably distorting its waveform is called _____	attenuator	an attenuator				eExam
☐	FBQ	An _____ filter consists of two reactive elements, one in series and one in parallel	L	L				eExam
☐	FBQ	A narrow region around the PN junction formed by the diffusion of majority carriers across the junction is called the _____ layer.	depletion	space-charge				eExam
☐	FBQ	In a linear network, having several sources (which include the equivalent source due to initial conditions), the overall response, at any point in the network, is equal to the sum of individual responses of each source considered separately, the other sources being made inoperative. This the _____ theorem of electrical network	superposition	superposition				eExam

☐								
☐	FBQ	"Insofar as load is concerned, any one-port network of resistance elements and energy sources can be replaced by a series combination of an ideal voltage source V and resistance R, where V is the open-circuit voltage of the one-port and R is the ratio of the open-circiut voltage to the short-circuit current". This is _____ theorem	Thevenin's	Thevenin				eExam
☐	FBQ	If a parallel combination of $$12\Omega$$ and $$6\Omega$$ resistances is connected to a series combination a $$42V$$ d.c. source and a $$3\Omega$$ resistance, the current in the $$12\Omega$$ resistance (to the nearest whole number) is _____ A	2	2				eExam
☐	FBQ	Two one-ports are _____ if they present the same v-I characteristics	equivalent	equivalent				eExam
☐	FBQ	The statement "the algebraic sum of the currents into a node at an instant is zero" is _____ current	Kirchhoff's	Kirchhoff's				eExam
☐	FBQ	Is a Klystron a Vacuum Tube? _____	yes	YES				eExam
☐	FBQ	the two types of bipolar juction transistors are _____ and _____ transistors	NPN, PNP	PNP, NPN				eExam

☐								
☐	FBQ	The dual of an N Channel field effect transistor is a _____ channel field effect transistor	P	P				eExam
☐	FBQ	Germanium, Silicon, Gallium Arsenide and Silicon Carbide are all examples of _____ materials	semiconductor	semiconductor				eExam
☐	FBQ	If a twisted pair transmission line is balanced write BALANCED, otherwise write UNBALANCED in this space provided _____	BALANCED	BALANCED				eExam
☐	FBQ	The theorem which is frequently called “the parallel generator theorem” is the _____ theorem	Millman's	Millman				eExam
☐	FBQ	Another name for Maximum Power theorem is _____ law	Jacobi's	Jacobi				eExam
☐	FBQ	At resonance, the _____ and _____ reactances of an LC circuit are equal	capacitive, inductive	inductive, capacitive				eExam
☐	FBQ	The theorem which states that the reactance of a passive, lossless one-port network always monotonically increases with frequency is called the _____ reactance theorem	Foster's	Foster				eExam

☐								
☐	FBQ	A bipolar junction transistor is basically a _____ - terminal device	three	3				eExam
☐	FBQ	Transistors are generally classified as _____ and _____ transitors	bipolar junction , field effect	field effect, bipolar junction				eExam
☐	FBQ	The _____ diode is used for the construction of a voltage regulator	Zener	zener				eExam
☐	FBQ	The conection of the positive terminal of a battery to the P-side and negative terminal to the N-side of a PN junction is referred to as _____ bias	reverse	reverse				eExam
☐	FBQ	The process whereby a AC voltage is converted to a unidirectional (DC) voltage is refered to as _____	rectification	rectification				eExam
☐	FBQ	The early electronic devices (diodes, triodes, etc) depended on _____ effect for the generation of current carriers (electrons)	thermionic	thermionic				eExam
☐	FBQ	The first diodes were made of _____ tubes	vacuum	vacuum				eExam
☐	FBQ	Energy stored in the form of a magnetic field or a moving charge in the _____	inductor	inductor				eExam

☐								
☐	FBQ	Which of the following circuit quantities is employed in the storage of energy? _____ (resistance, capacitance, conductance, resistivity)	capacitance	capacitance				eExam
☐	FBQ	Given that $$i=Gv$$, where $$i$$ is the current and $$v$$ is the potential difference, then the unit of $$G$$ is _____ (ohms, siemens, ampres, volts)	siemens	siemens				eExam
☐	FBQ	The electron gun of a cathode ray tube provides a beam of high velocity electron. If the electrons are accelerated through a potential difference of 20 000 eV over adistance of 4 cm, then the field strength is _____ $$\times{10^{5}} V/m$$ (2, 3, 4, 5)	5	5				eExam
☐	FBQ	The quantity $$\int \vec{B}\cdot{d}\vec{A}$$ defines the _____ (magnetic flux density, electric current density, magnetic field strength, magnetic flux)	magnetic flux	magnetic flux				eExam
☐	FBQ	the potential gradient is a measure of the _____ (electric current, magnetic flux density, electric flux, electric field strength)	electric field strength	electric field strength				eExam

☐								
☐	FBQ	The energy transfer capability of the flow of electric charge is determined by the _____ through which the charge moves (resistance, potential difference, impedance, current)	potential difference	potential difference				eExam
☐	FBQ	A circuit device which changes or information to another is called _____ (transducer, modulator, oscillator, amplifier)	transducer	transducer				eExam
☐	FBQ	When the dimensions of a network component s unimportant and its total effect can be considered to be concentrated at a poin, then the component can be represented by a _____ parameter (lumped, distributed, continuous, discrete)	lumped	lumped				eExam
☐	FBQ	A transistor _____ , _____ device (active, linear; passive, nonlinear; passive, linear; active, non-linear)	active, non-linear	active, non-linear				eExam
☐	FBQ	A two- terminal device is a _____ - port (one, two, three, four)	one	one				eExam
☐	FBQ	Transistors are _____ -ports. (tow, three, four, one)	two	two				eExam
☐	FBQ	A diode is a _____ - terminal device (one, two, three, four)	two	two				eExam

☐								
☐	FBQ	Attenuation is measured in units of _____	decibels	decibel				
☐	FBQ	Attenuators used with coaxial lines are the _____ form while attenuators for use with twisted pair are required to be the _____ form.	unbalanced, balanced	unbalanced, balanced				
☐	FBQ	Frequency bandwidth is expressed in units of _____	hertz	hertz				
☐	FBQ	A filter in which the signal passes through an inductor, or in which a capacitor provides a path to ground, presents less attenuation to low-frequency signals than high-frequency signals and is a _____ filter	low-pass	low-pass				
☐	FBQ	Linear filters whose implementation is based on the combination of resistors (R), inductors (L) and capacitors (C) are collectively known as _____ filters	passive	passive				
☐	FBQ	For a series RLC circuit, if $$f=\frac{1}{2\pi\sqrt{LC}}$$, $$f$$ is the _____ frequency	resonant	resonance				
☐	FBQ	In a series RLC circuit, the capacitive reactance causes total current to _____ the applies voltage.	lead	lead				

☐								
☐	FBQ	The electrical properties of semiconductors can be modified by addition of impurities to the pure semiconductor substrate. This process is known as [ ]	doping	doping				
☐	FBQ	For reactive loads, maximum power transfer takes place when the source impedance is the complex [ ] of the load impedance	conjugate	conjugate				
☐	FBQ	Electrical impedance has both magnitude and [ ] angle	phase	phase				
☐	FBQ	The impedance of a lossless idealized network element is referred to as [ ]	reactance	reactance				
☐	FBQ	The conduction mechanism in semiconductors is contributed to by both electrons and [ ]	holes	holes				
☐	FBQ	Circuit elements which have a linear voltage to current relationship and which obey Ohm's Law are referred to as [ ] devices	ohmic	ohmic				
☐	FBQ	An electronic device that reduces the amplitude or power of a signal without appreciably distorting its waveform is called [ ]	attenuator	an attenuator				
☐	FBQ	An [ ] filter consists of two reactive elements, one in series and one in parallel	L	L				

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☐	FBQ	A narrow region around the PN junction formed by the diffusion of majority carriers across the junction is called the [ ] layer.	depletion	space-charge				
☐	FBQ	In a linear network, having several sources (which include the equivalent source due to initial conditions), the overall response, at any point in the network, is equal to the sum of individual responses of each source considered separately, the other sources being made inoperative. This the [ ] theorem of electrical network	superposition	superposition				
☐	FBQ	"Insofar as load is concerned, any one-port network of resistance elements and energy sources can be replaced by a series combination of an ideal voltage source V and resistance R, where V is the open-circuit voltage of the one-port and R is the ratio of the open-circiut voltage to the short-circuit current". This is [ ] theorem	Thevenin's	Thevenin				
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☐								
☐	FBQ	Two one-ports are _____ if they present the same v-I characteristics	equivalent	equivalent				
☐	FBQ	The statement "the algebraic sum of the currents into a node at an instant is zero" is _____ current	Kirchhoff's	Kirchhoff's				
☐	FBQ	Is a Klystron a Vacuum Tube? _____	yes	YES				
☐	FBQ	the two types of bipolar juction transistors are _____ and _____ transistors	NPN, PNP	PNP, NPN				
☐	FBQ	The dual of an N Channel field effect transistor is a _____ channel field effect transistor	P	P				
☐	FBQ	Germanium, Silicon, Gallium Arsenide and Silicon Carbide are all examples of _____ materials	semiconductor	semiconductor				
☐	FBQ	If a twisted pair transmission line is balanced write BALANCED, otherwise write UNBALANCED in this space provided _____	BALANCED	BALANCED				
☐	FBQ	The theorem which is frequently called “the parallel generator theorem” is the _____ theorem	Millman's	Millman				

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☐	FBQ	Another name for Maximum Power theorem is [ ] law	Jacobi's	Jacobi				
☐	FBQ	At resonance, the [ ] and [ ] reactances of an LC circuit are equal	capacitive, inductive	inductive, capacitive				
☐	FBQ	The theorem which states that the reactance of a passive, lossless one-port network always monotonically increases with frequency is called the [ ] reactance theorem	Foster's	Foster				
☐	FBQ	A bipolar junction transistor is basically a [ ] - terminal device	three	3				
☐	FBQ	Transistors are generally classified as [ ] and [ ] transitors	bipolar junction , field effect	field effect, bipolar junction				
☐	FBQ	The [ ] diode is used for the construction of a voltage regulator	Zener	zener				
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☐	FBQ	The process whereby a AC voltage is converted to a unidirectional (DC) voltage is refered to as _____	rectification	rectification				
☐	FBQ	The early electronic devices (diodes, triodes, etc) depended on _____ effect for the generation of current carriers (electrons)	thermionic	thermionic				
☐	FBQ	The first diodes were made of _____ tubes	vacuum	vacuum				
☐	FBQ	Energy stored in the form of a magnetic field or a moving charge in the _____	inductor	inductor				
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☐	FBQ	Given that $$i=Gv$$, where $$i$$ is the current and $$v$$ is the potential difference, then the unit of $$G$$ is _____ (ohms, siemens, ampres, volts)	siemens	siemens				
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Showing 1 to 150 of 300 entries

Previous 1 2 Next